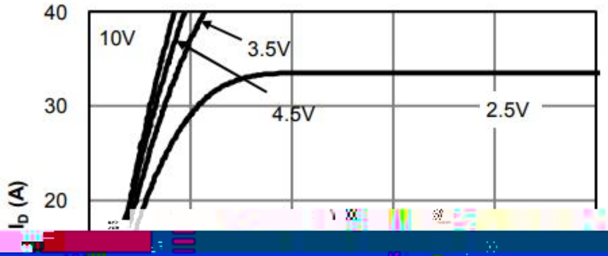
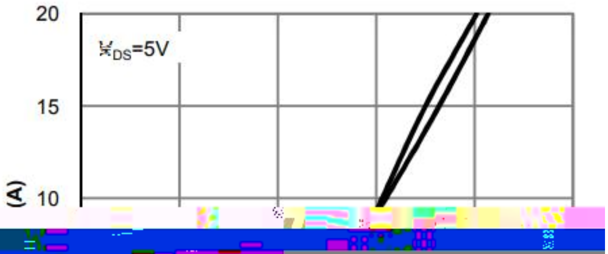
Rev.A Sep.-2021

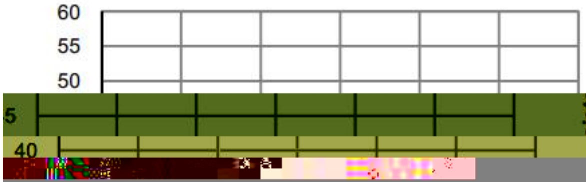
SOT23-3 N MOS
- CHANNEL MOSFET in a SOT23-3 Plastic Package.

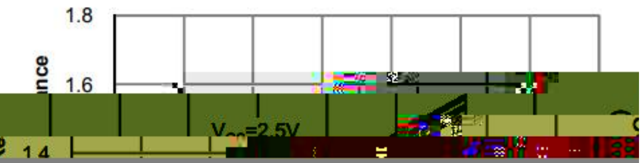
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	±10	V
Drain Current – Continuous		I_D	4.5	A
Pulsed Drain Current		I_{DM}	12	A
Power Dissipation		P_D	1.4	W
Storage Temperature Range		T_{stg}	-55～150	℃
Maximum Junction-to-Ambient	t ≤ 10s	$R_{θJA}$	90	℃/W
Maximum Junction-to-Ambient				

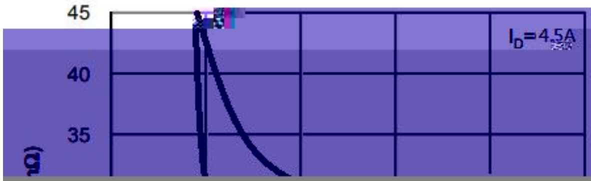
Parameter	Symbol	Test Conditions	[redacted]	[redacted]	[redacted]	Unit
Total Gate Charge	Qg(10V)	V_{GS}=10V, V_{DS}=10V I_D=4.5A	[redacted]	[redacted]	[redacted]	
Total Gate Charge	Qg(4.5V)		[redacted]	[redacted]	[redacted]	nC
Gate Source Charge	Qgs		[redacted]	[redacted]	[redacted]	
Gate Drain Charge	Qgd		[redacted]	[redacted]	[redacted]	
Turn–On Delay Time	$t_{d(on)}$	V_{GS}=10V, V_{DS}=10V R_{GEN}=3Ω R_L=1.7Ω	[redacted]	[redacted]	[redacted]	ns
Turn–On Rise Time	t_r		[redacted]	[redacted]	[redacted]	
Turn–Off Delay Time	$t_{d(off)}$			20		
Turn–Off Fall Time	[redacted]			6		

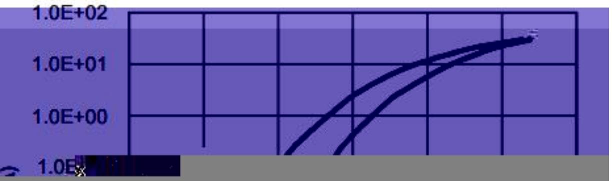

40
30
20
I_D (A)
10V
3.5V
4.5V
2.5V

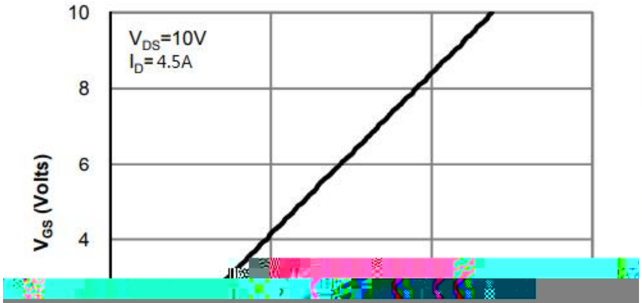

20
15
10
(A)
V_DS=5V


60
55
50
5
40


1.8
1.6
1.4
nce
sista
Re
V_GS=2.5V


45
40
35
Ω)
I_D=4.5A


1.0E+02
1.0E+01
1.0E+00
1.0E



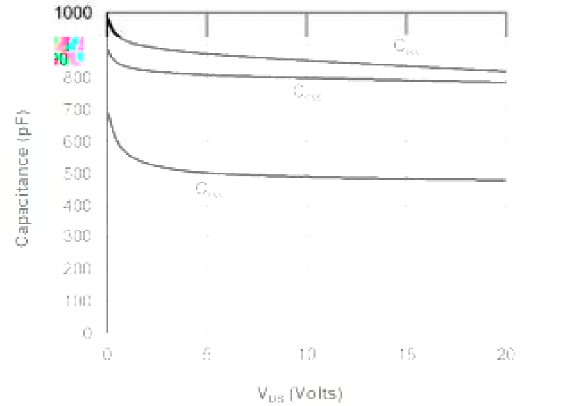
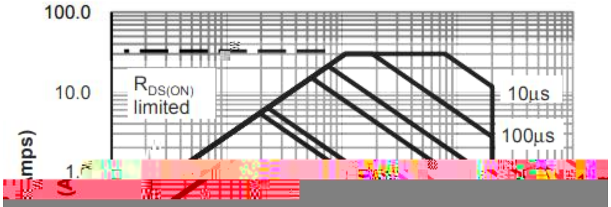
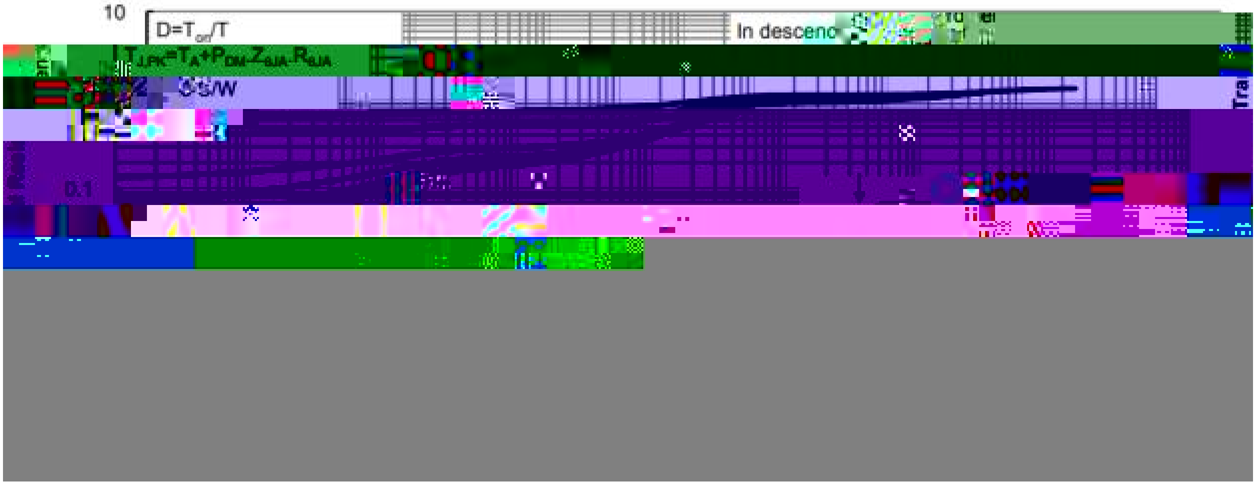
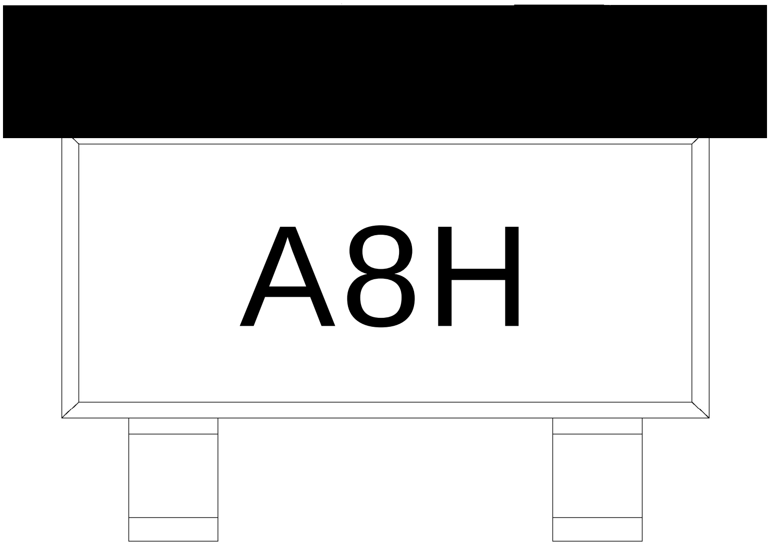


Figure 8: Capacitance Characteristics







A8:

H:

Note:

A8	Product Type Code
H:	Company Code.

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1 150